

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of:

Docket No. P27157

Haujie CHEN, *et al.*

Confirmation No. 4303

Appln. No. : 10/689,506

Group Art Unit: 2813

Filed : October 20, 2003

Examiner: J. M. Mitchell

For : HIGH PERFORMANCE STRESS-ENHANCED MOSFETs USING Si:C
AND SiGe EPITAXIAL SOURCE/DRAIN AND METHOD OF
MANUFACTURE

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop AF
Randolph Building
401 Dulany Street
Alexandria VA 22314

AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the final Office Action dated October 11, 2006, Applicants request reconsideration of the rejected claims in view of the following amendments and remarks.

Amendments to the claims begin on page 2; and

Remarks begin on page 7.

If extensions of time are necessary to prevent abandonment of this application, then such extensions of time are hereby petitioned under 37 C.F.R. § 1.136(a), and any fees required therefore (including fees for net addition of claims) are hereby authorized to be charged to Deposit Account No. 09-0458.